



## General Description

The HAM6968N is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications. The meet the RoHS and Product requirement with full function reliability approved.



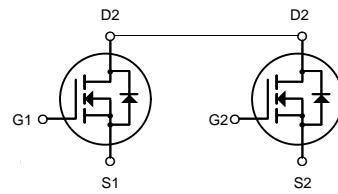
TSSOP-8

## General Features

$V_{DS} = 20V$   $I_D = 6A$

$R_{DS(ON)} < 27m\Omega$  @  $V_{GS}=4.5V$

$R_{DS(ON)} < 37m\Omega$  @  $V_{GS}=2.5V$



## Application

Dual N-Channel MOSFET

Battery protection

Load switch

Uninterruptible power supply

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HAM6968N	TSSOP-8	HXY MOSFET	5000

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current-Continuous	6	A
$I_{DM}$	Drain Current-Pulsed <sup>(Note 1)</sup>	25	A
$P_D$	Maximum Power Dissipation	1.5	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	83	°C/W



**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	21	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =19.5V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R <sub>D(S)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A	-	21	27	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.5A	-	27	37	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =4.5A	-	10	-	S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =8V, V <sub>GS</sub> =0V, F=1.0MHz	-	600	-	PF
Output Capacitance	C <sub>oss</sub>		-	330	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	140	-	PF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =1A V <sub>GS</sub> =4.5V, R <sub>GEN</sub> =6Ω	-	10	20	nS
Turn-on Rise Time	t <sub>r</sub>		-	11	25	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	35	70	nS
Turn-Off Fall Time	t <sub>f</sub>		-	30	60	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =6A, V <sub>GS</sub> =4.5V	-	10	15	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.5	-	nC
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>s</sub> =1.7A	-	0.75	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>s</sub>		-	-	1.7	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production



### Typical Characteristics

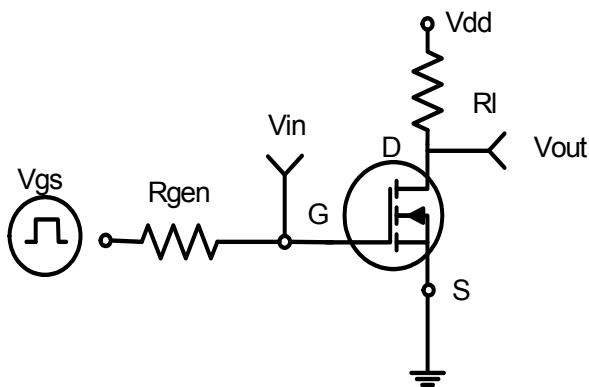


Figure 1:Switching Test Circuit

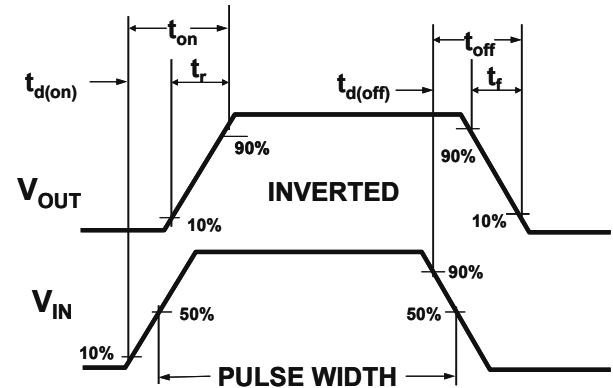


Figure 2:Switching Waveforms

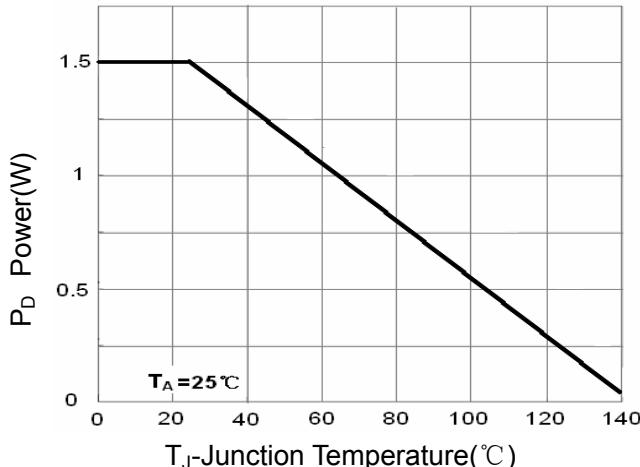


Figure 3 Power Dissipation

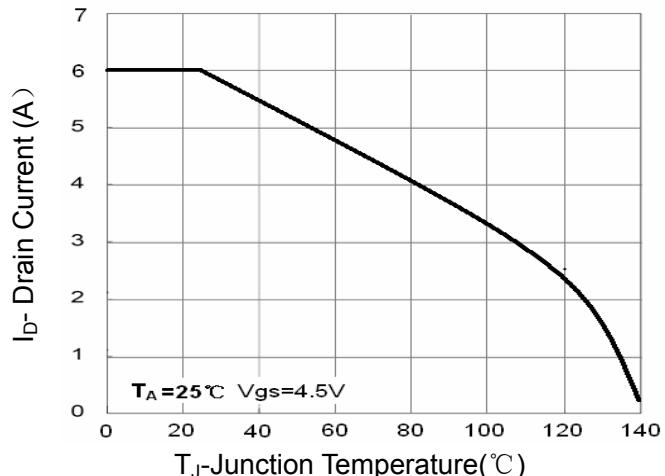


Figure 4 Drain Current

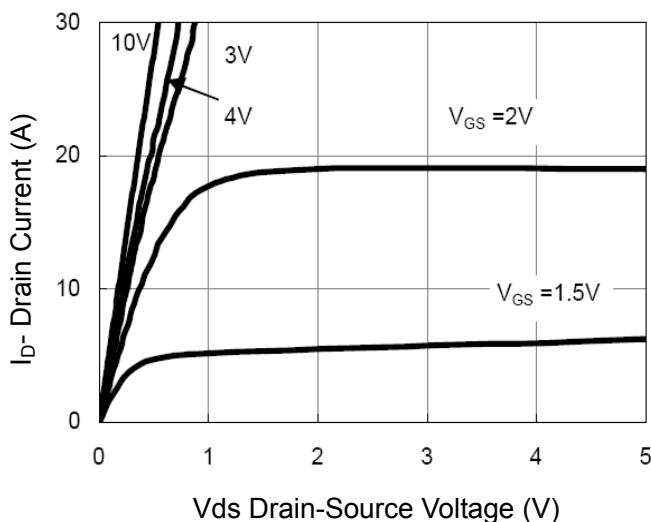


Figure 5 Output Characteristics

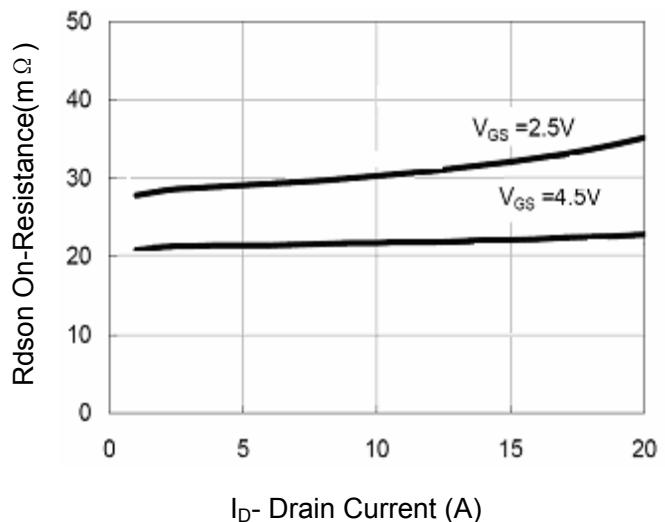


Figure 6 Drain-Source On-Resistance

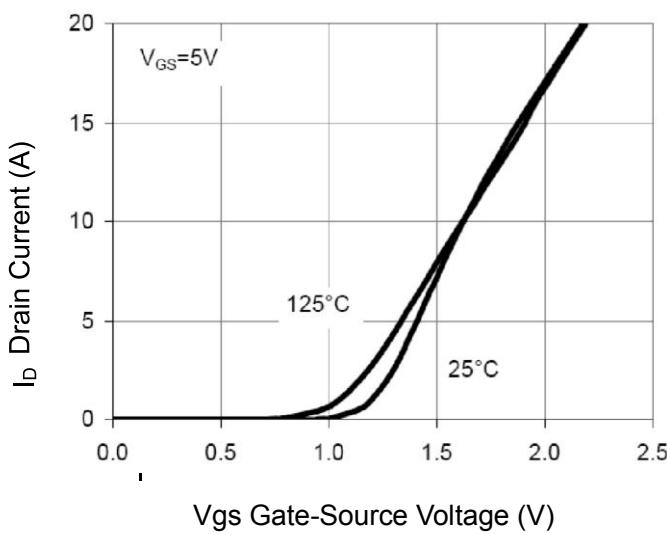


Figure 7 Transfer Characteristics

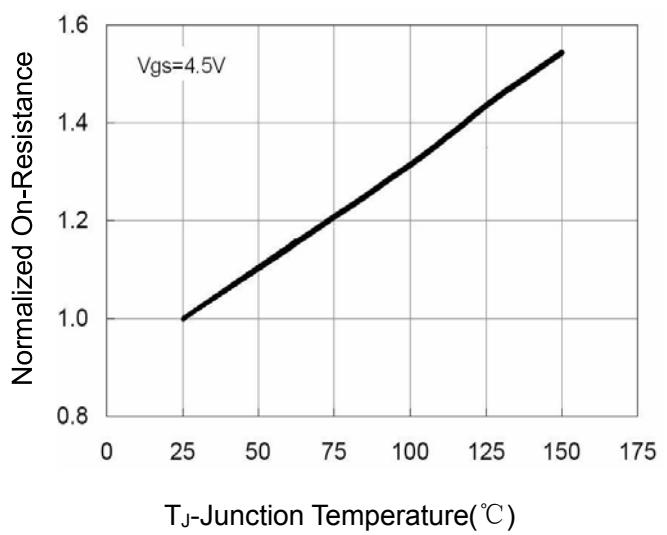


Figure 8 Drain-Source On-Resistance

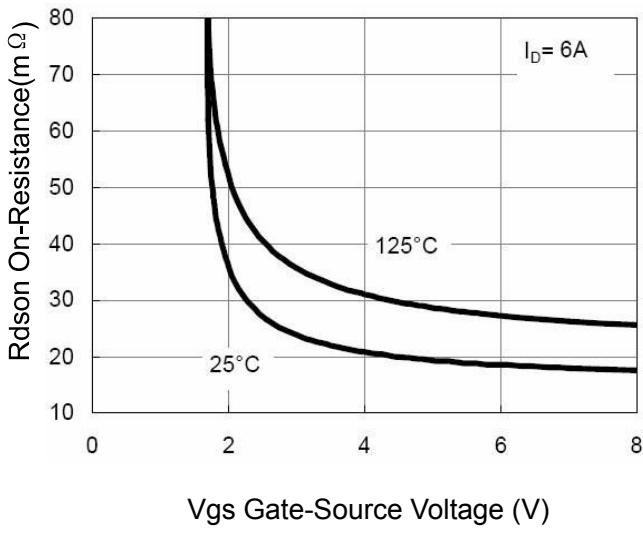


Figure 9 Rdson vs Vgs

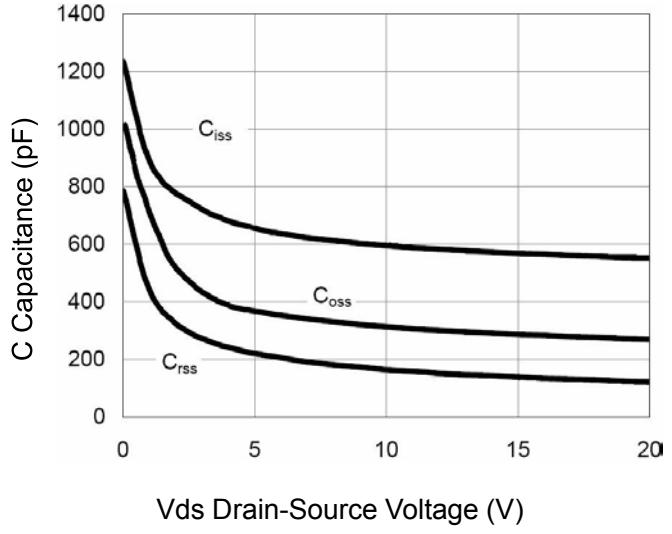


Figure 10 Capacitance vs Vds

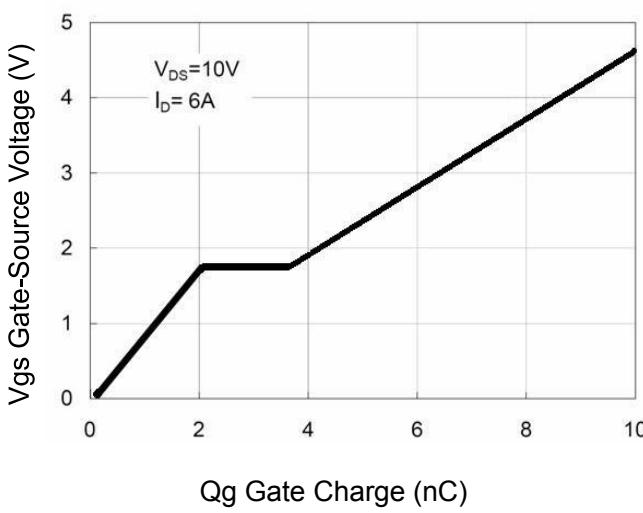


Figure 11 Gate Charge

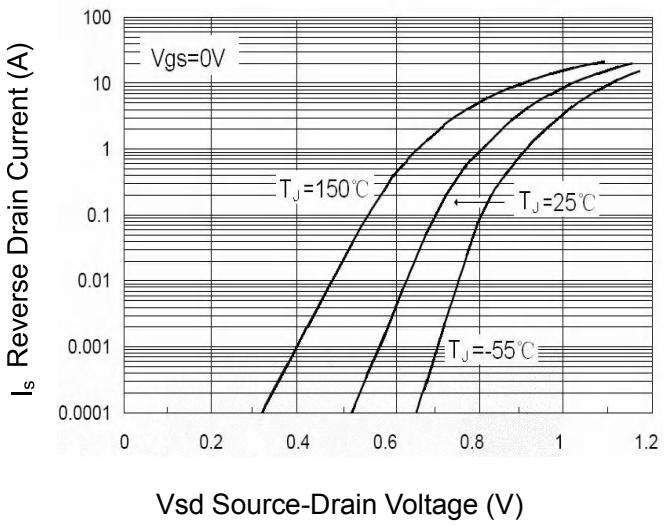
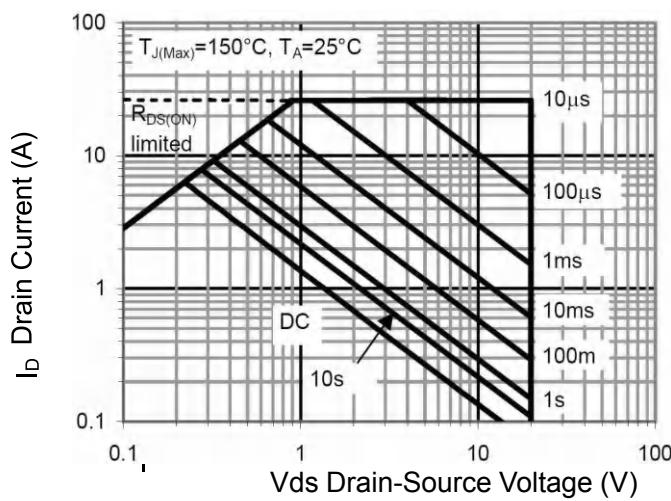
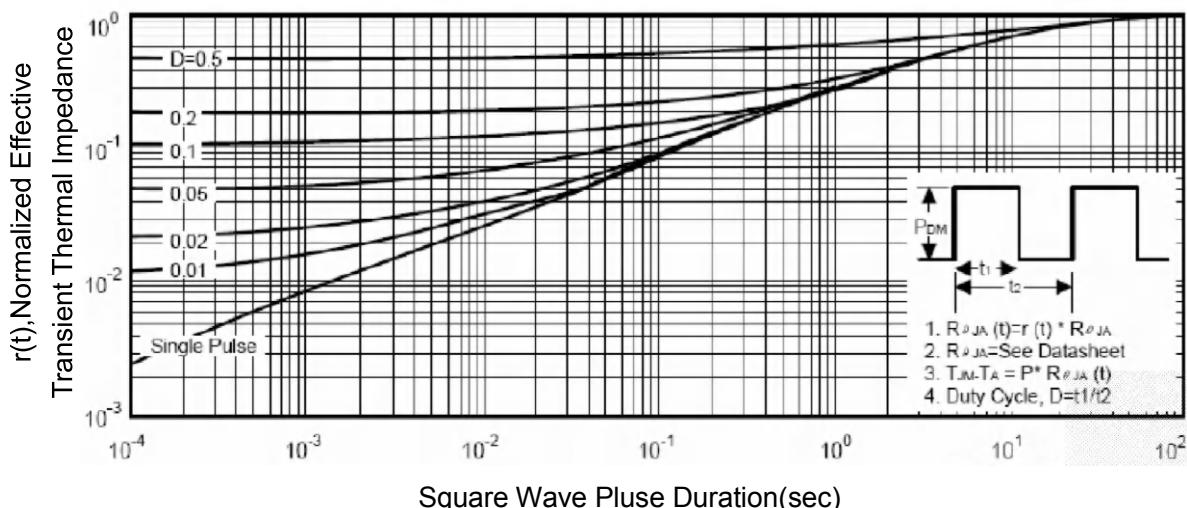


Figure 12 Source- Drain Diode Forward



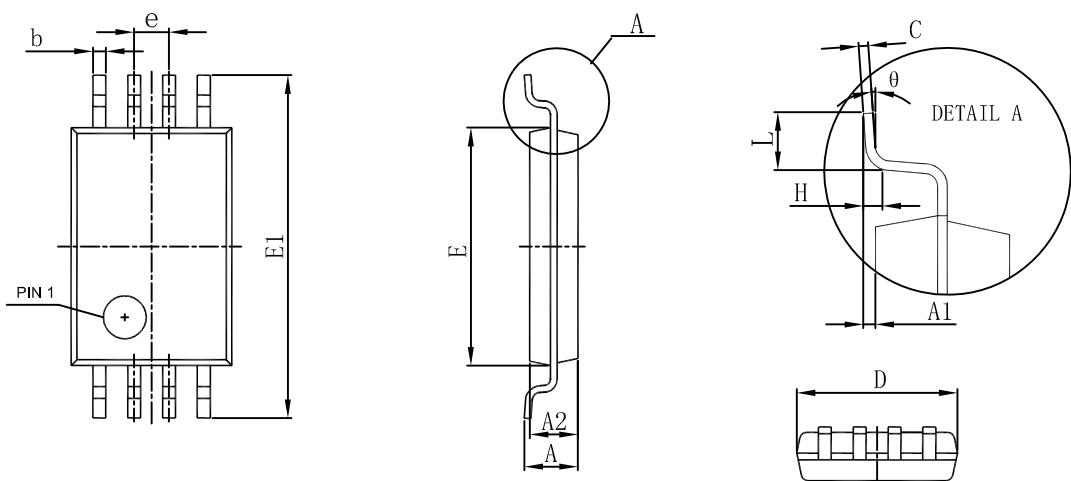
### Figure 13 Safe Operation Area



**Figure 14 Normalized Maximum Transient Thermal Impedance**



### TSSOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.200		0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°



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